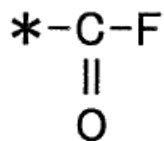


ABSTRACT

Provided is an etching method capable of selectively etching an oxide. The etching method includes an etching step
5 in which an etching target (12) including an oxide is placed in a chamber (10), and the oxide included in the etching target (12) is etched in the chamber (10) using an etching gas containing a fluorine-containing compound including a functional group represented by a chemical formula below.
10 The oxide is at least one of a metal oxide or a semimetal oxide. In the etching step, the etching is performed without generating a plasma of the etching gas in the chamber (10).
[Chem. 1]



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FIG. 1